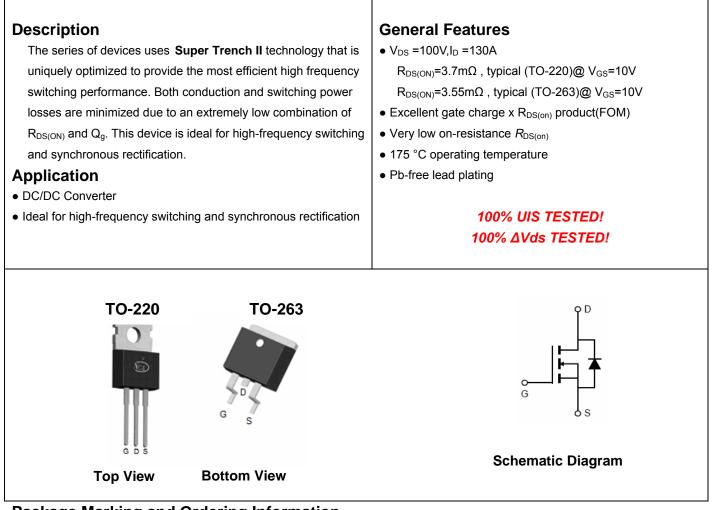


NCE N-Channel Super Trench II Power MOSFET



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP040N10M	NCEP040N10M	TO-220-3L			
NCEP040N10MD	NCEP040N10MD	TO-263-2L	-	-	-

Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	100	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	Ι _D	130	А
Drain Current-Continuous(T _C =100℃)	I _D (100℃)	100	А
Pulsed Drain Current ^(Note 1)	I _{DM}	520	А
Maximum Power Dissipation	PD	210	W
Derating factor		1.4	W/°C
Single pulse avalanche energy (Note 5)	E _{AS}	750	mJ
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 175	°C



Thermal Characteristic

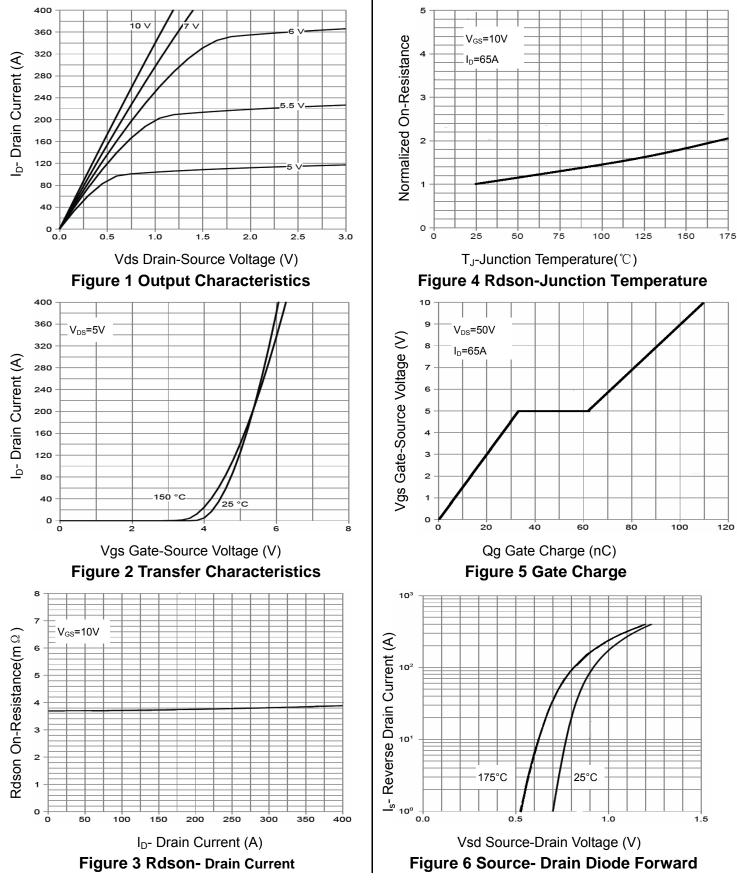
Thermal Resistance, Junction-to-Case ^(Note 2)			0.71		°C/W		
Electrical Characteristics (Tc=	=25℃unless	otherwise note	ed)				
Parameter	Symbol	Condition		Min	Тур	Max	Unit
Off Characteristics	·						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA		100		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V,V _{GS} =0V		-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V		-	-	±100	nA
On Characteristics (Note 3)	·						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =28	50µA	2	3	4	V
Drain-Source On-State Resistance	Б	N/ 401/ L 05A	TO-220	-	3.7	4.0	mΩ
Dian-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =65A	TO-263		3.55	4.0	mΩ
Forward Transconductance	g fs	V _{DS} =5V,I _D =65A			130	-	S
Dynamic Characteristics (Note4)							
Input Capacitance	C _{lss}	V _{DS} =50V,V _{GS} =0V, F=1.0MHz		-	6300	-	PF
Output Capacitance	C _{oss}			-	560	-	PF
Reverse Transfer Capacitance	C _{rss}			-	40	-	PF
Switching Characteristics (Note 4)							
Turn-on Delay Time	t _{d(on)}			-	23	-	nS
Turn-on Rise Time	tr	V _{DD} =50V,I _D =6	V _{DD} =50V,I _D =65A,		15	-	nS
Turn-Off Delay Time	t _{d(off)}	V _{GS} =10V,R _G =	=3Ω	-	48	-	nS
Turn-Off Fall Time	t _f			-	16	-	nS
Total Gate Charge	Qg	V _{DS} =50V,I _D =65A, V _{GS} =10V		-	110	-	nC
Gate-Source Charge	Q _{gs}			-	33		nC
Gate-Drain Charge	Q _{gd}			_	30		nC
Drain-Source Diode Characteristics	·						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =65A		-		1.2	V
Diode Forward Current (Note 2)	I _S			-	-	130	Α
Reverse Recovery Time	t _{rr}	$T_J = 25^{\circ}C, I_F = 65A$ di/dt = 100A/µs ^(Note3)		-	70	-	nS
Reverse Recovery Charge	Qrr			-	117	-	nC

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width ≤ 300 μ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25 $^\circ C$,V_DD=50V,V_G=10V,L=0.5mH,Rg=25 Ω

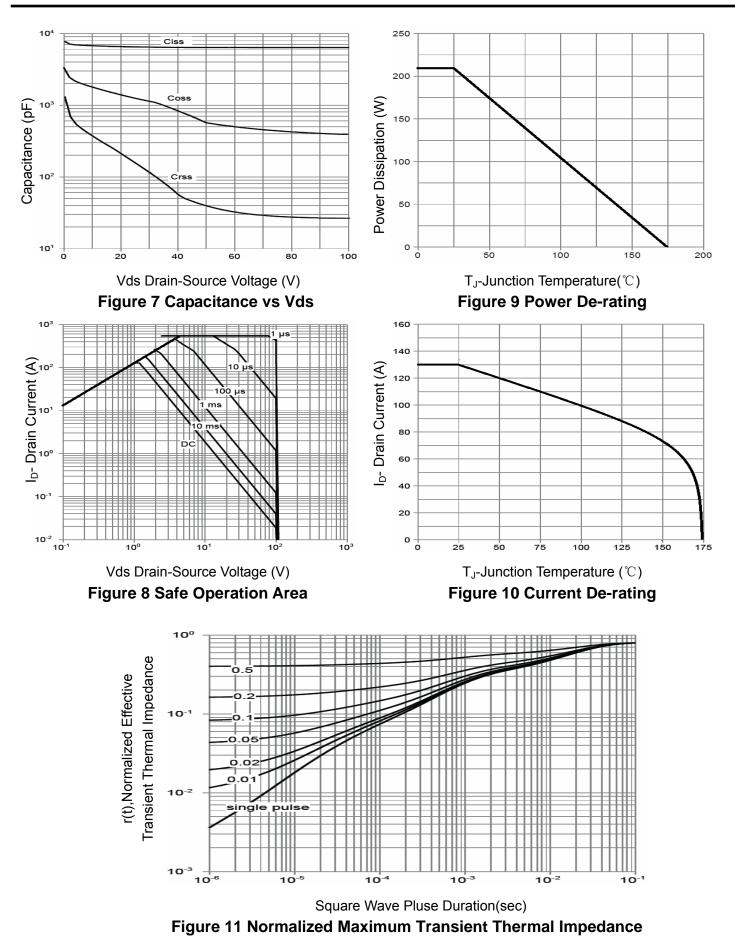


Typical Electrical and Thermal Characteristics



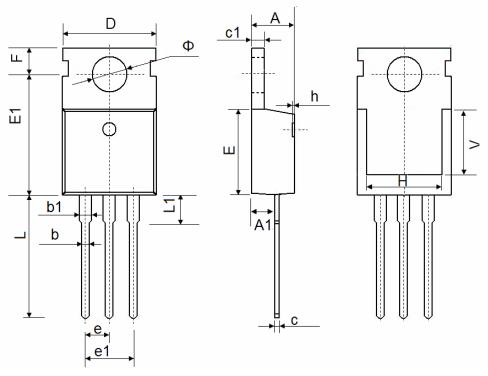


NCEP040N10M,NCEP040N10MD





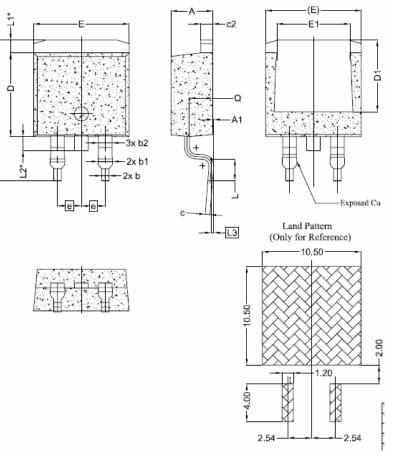
TO-220-3L Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540 TYP.		0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	6.900 REF.		0.276 REF.		
Φ	3.400	3.800	0.134	0.150	



TO-263-2L Package Information



SYMBOL	DIMENSIONS				
STMBOL	MIN.	NOM.	MAX.		
Α	4.24	4.44	4.64		
A1	0.00	0.10	0.25		
b	0.70	0.80	0.90		
b1	1.20	1.55	1.75		
b2	1,20	1,45	1,70		
с	0.40	0.50	0.60		
c2	1,15	1,27	1,40		
D	8.82	8.92	9.02		
D1	6.86	7.65	_		
E	9.96	10.16	10.36		
E1	6.89	7.77	7.89		
е	2.54 BSC				
н	14,61	15,00	15,88		
L	1.78	2.32	2.79		
L1	1.36 REF.				
L2	1.50 REF.				
L3	0.25 BSC				
Q	2.30	2.48	2.70		



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